N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
30	0.0039 at V_{GS} = 10 V	107[d]	67
	0.0045 at V_{GS} = 4.5 V	103[d]	

FEATURES

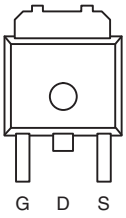
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

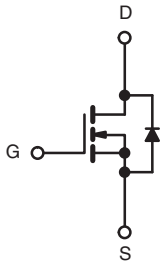
- DC/DC Converters
  - Synchronous Buck Low Side

TO-252



Top View

Drain Connected to Tab



N-Channel MOSFET

Ordering Information: SUD42N03-3m9P-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	T_C = 25 °C (Silicon Limited)	I_D	107[d]	A
	T_C = 70 °C (Silicon Limited)		85[d]	
	T_C = 25 °C (Package Limited)		42	
Pulsed Drain Current (t = 300 µs)		I_{DM}	120	
Avalanche Current		I_{AS}	45	
Single Avalanche Energy[a]	L = 0.1 mH	E_{AS}	101	mJ
Maximum Power Dissipation[a]	T_C = 25 °C	P_D	73.5[b]	W
	T_A = 25 °C[c]		2.5	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	50	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.7	

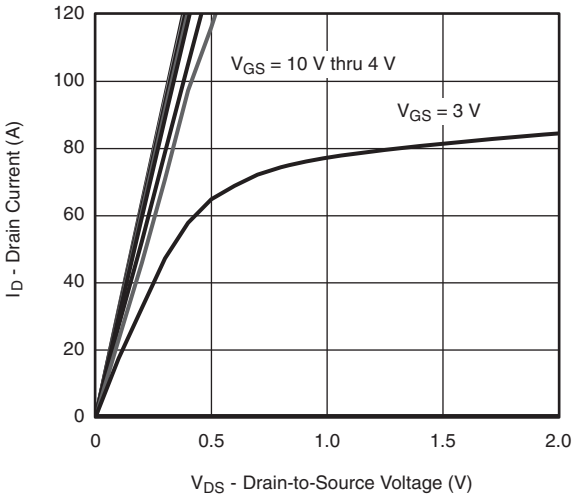
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR-4 material).
d. Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 42 A.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{DS} = 0 V, I_D = 250 µA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V			1	µA
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 30 V, V_{GS} = 0 V, T_J = 150 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 10 V, V_{GS} = 10 V	50			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 22 A		0.0032	0.0039	Ω
		V_{GS} = 4.5 V, I_D = 20 A		0.0037	0.0045	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 20 A		110		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz		3535		pF
Output Capacitance	C_{oss}			680		
Reverse Transfer Capacitance	C_{rss}			400		
Total Gate Charge[c]	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 20 A		67	100	nC
Gate-Source Charge[c]	Q_{gs}			10.5		
Gate-Drain Charge[c]	Q_{gd}			12.2		
Gate Resistance	R_g	f = 1 MHz	0.3	1.4	2.8	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 15 V, R_L = 1.5 Ω I_D ≅ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		11	20	ns
Rise Time[c]	t_r			10	20	
Turn-Off Delay Time[c]	$t_{d(off)}$			35	53	
Fall Time[c]	t_f			10	20	
Drain-Source Body Diode Ratings and Characteristics[b] T_C = 25 °C						
Continuous Current	I_S				42	A
Pulsed Current	I_{SM}				120	
Forward Voltage[a]	V_{SD}	I_F = 10 A, V_{GS} = 0 V		0.83	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 10 A, dI/dt = 100 A/µs		41	62	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2	3	A
Reverse Recovery Charge	Q_{rr}			40	60	nC

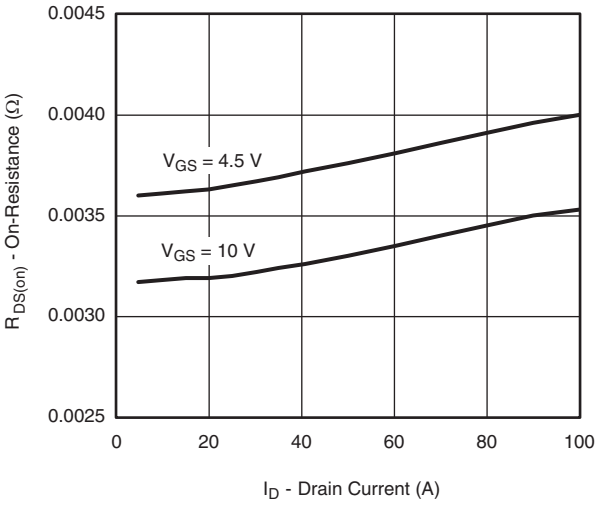
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

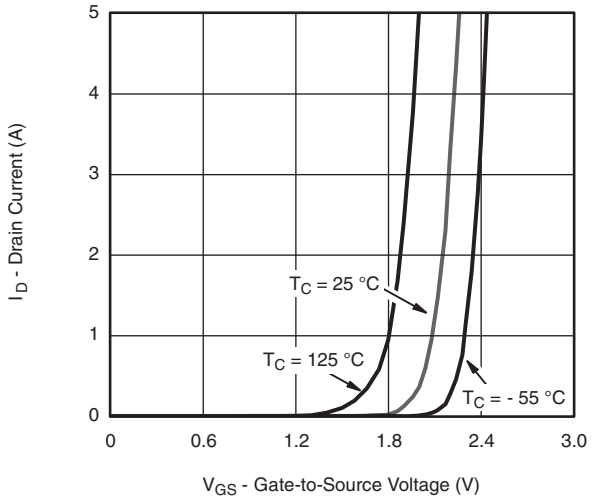
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



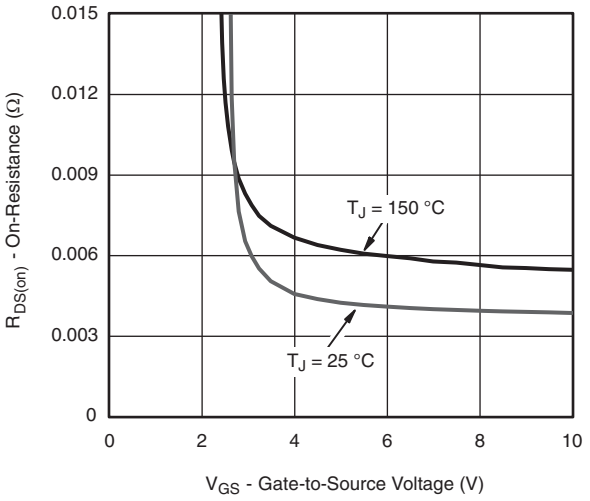
Output Characteristics



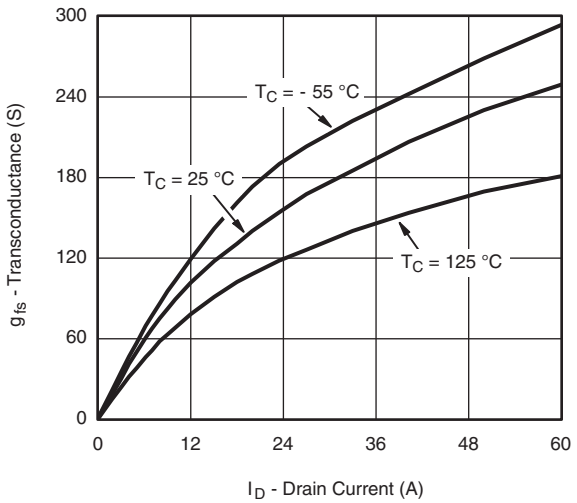
On-Resistance vs. Drain Current



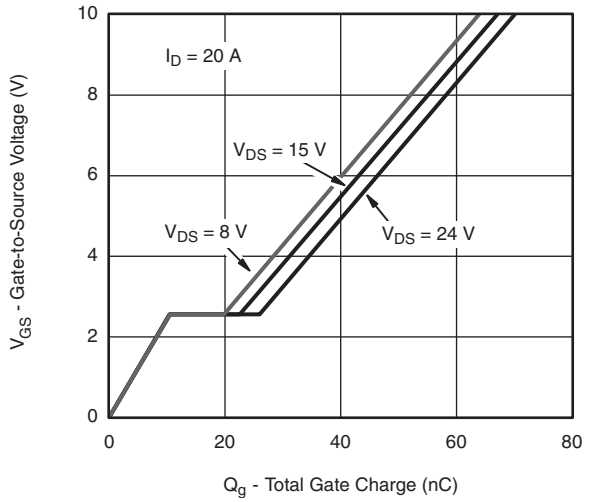
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage

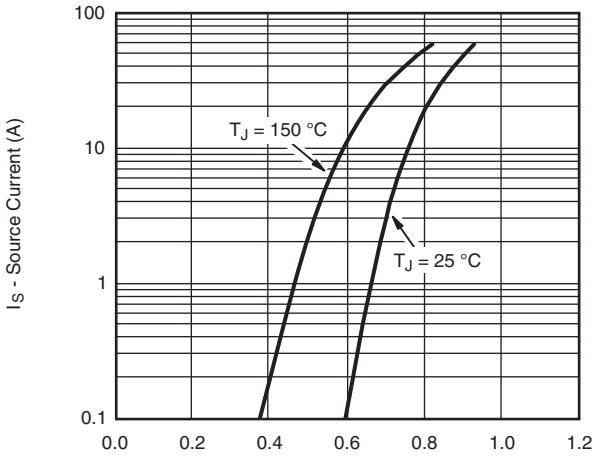


Transconductance

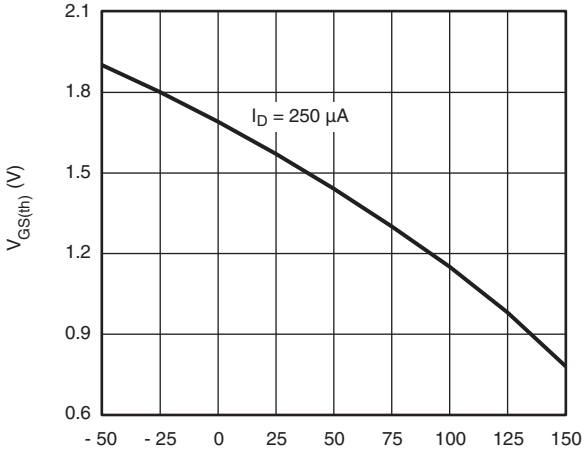


Gate Charge

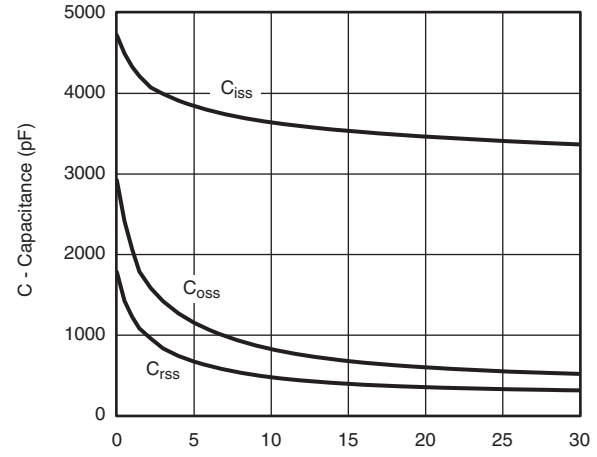
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



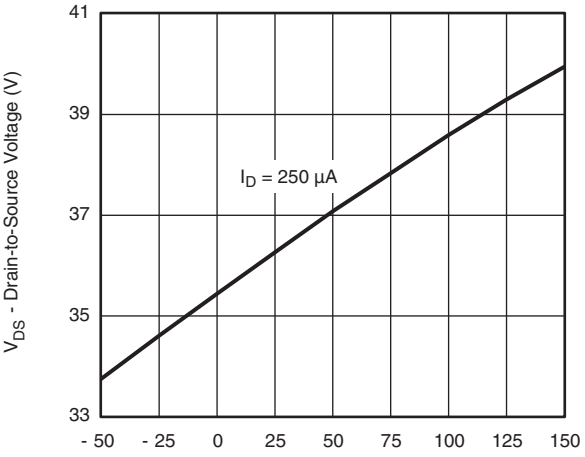
Source-Drain Diode Forward Voltage



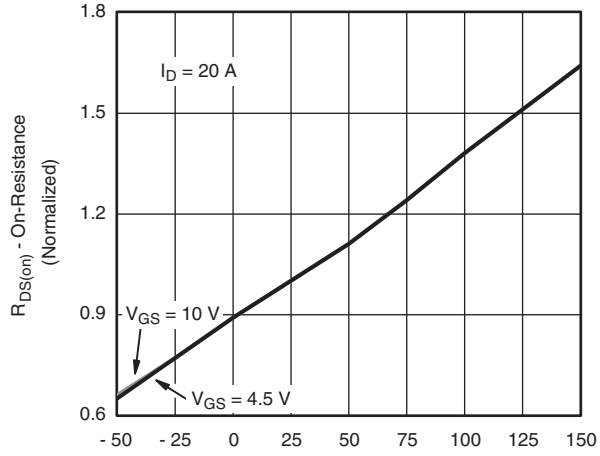
Threshold Voltage



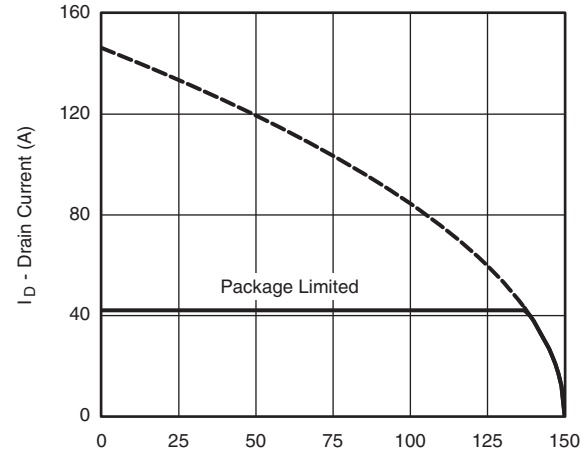
Capacitance



Drain Source Breakdown vs. Junction Temperature

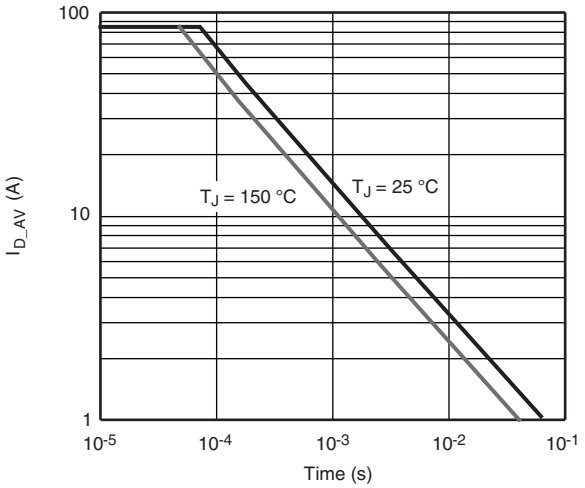


On-Resistance vs. Junction Temperature

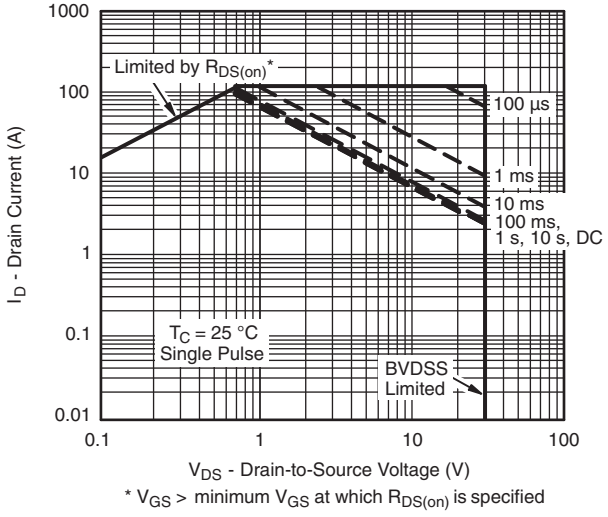


Current Derating

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

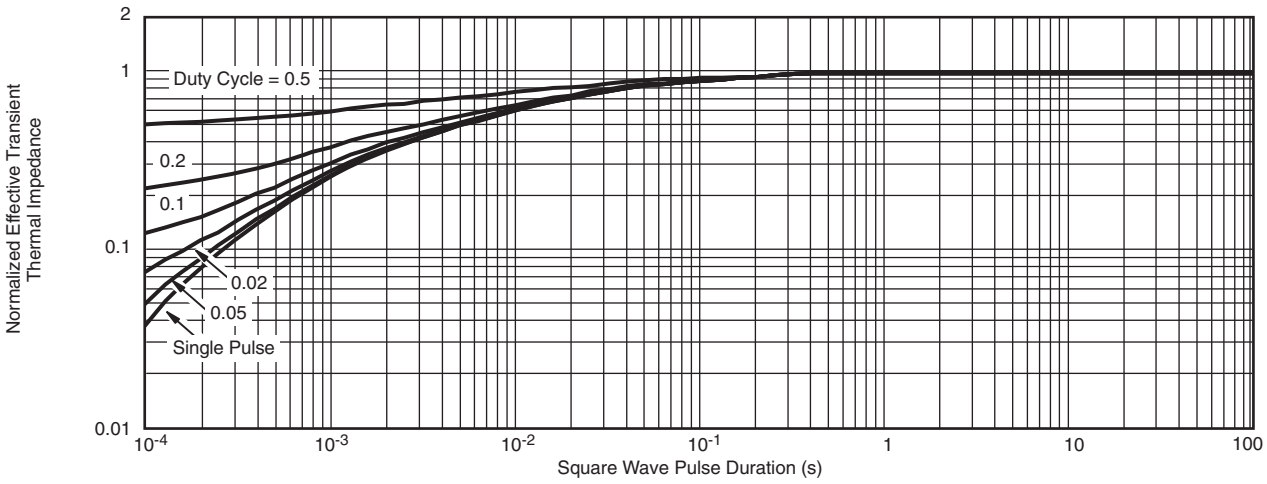


Single Pulse Avalanche Current Capability vs. Time



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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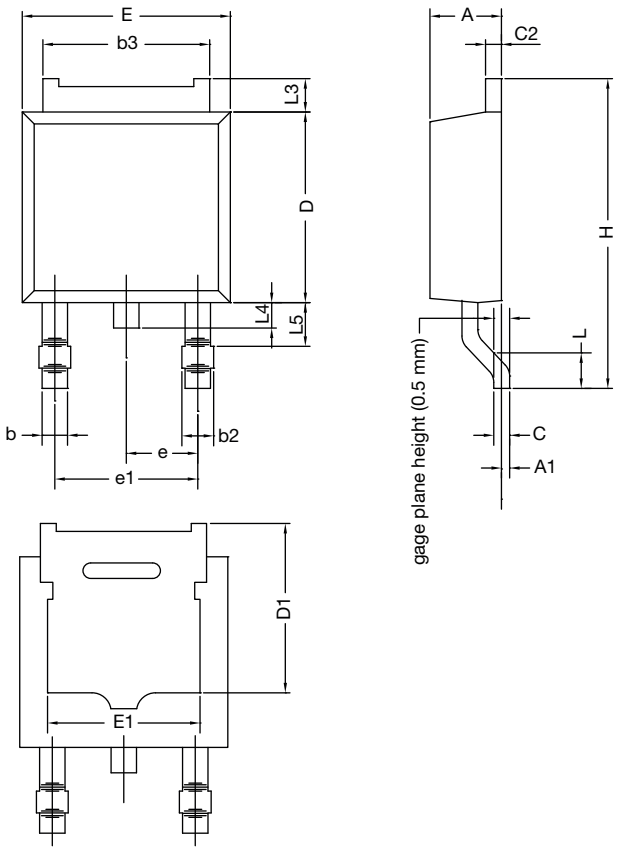
TO-252AA Case Outline

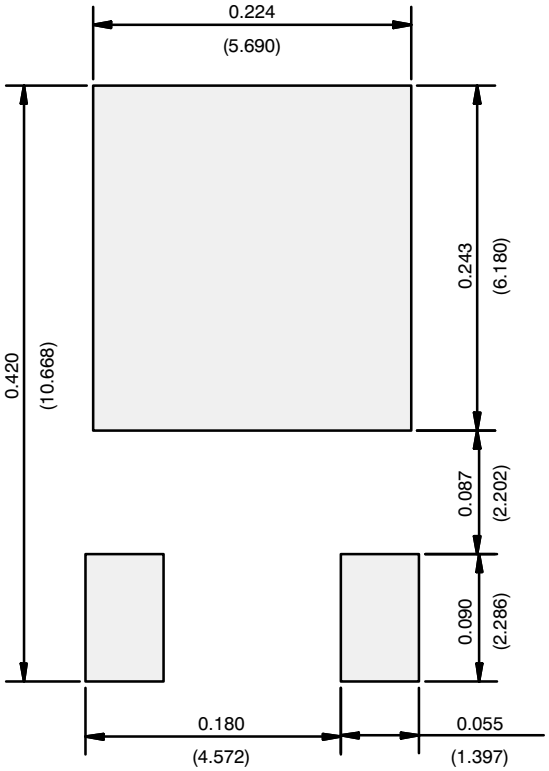


	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347				

Notes

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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